

Features

- 600 V, 30 A, Low Collector-Emitter Saturation Voltage ($V_{CE(sat)}$)
- Trench-Gate Field-Stop technology
- Optimized for conduction
- RoHS compliant*

Applications

- Switch-Mode Power Supplies (SMPS)
- Uninterruptible Power Sources (UPS)
- Power Factor Correction (PFC)
- Induction heating

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BIDW30N60T Insulated Gate Bipolar Transistor (IGBT)

General Information

The Bourns® Model BIDW30N60T IGBT device combines technology from a MOS gate and a bipolar transistor for an optimum component for high voltage and high current applications. This device uses Trench-Gate Field-Stop technology providing greater control of dynamic characteristics with a lower Collector-Emitter Saturation Voltage ($V_{CE(sat)}$) and fewer switching losses. In addition, this structure gives a lower thermal resistance $R_{(th)}$.

Additional Information

Click these links for more information:



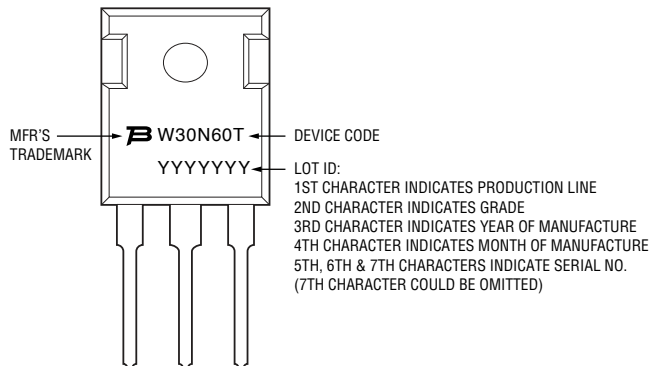
Maximum Electrical Ratings ($T_C = 25\text{ °C}$, unless otherwise specified)

Parameter	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CES}	600	V
Continuous Collector Current ($T_C = 25\text{ °C}$), limited by T_{jmax}	I_C	60	A
Continuous Collector Current ($T_C = 100\text{ °C}$), limited by T_{jmax}	I_C	30	A
Pulsed Collector Current, t_p limited by T_{jmax}	I_{CP}	90	A
Gate-Emitter Voltage	V_{GE}	± 20	V
Continuous Forward Current ($T_C = 25\text{ °C}$), limited by T_{jmax}	I_F	60	A
Continuous Forward Current ($T_C = 100\text{ °C}$), limited by T_{jmax}	I_F	30	A
Short-circuit Withstand Time ($V_{CE} = 300\text{ V}$, $V_{GE} = 15\text{ V}$)	T_{SC}	10	μs
Total Power Dissipation	P_{total}	230	W
Storage Temperature	T_{STG}	-55 to +150	$^{\circ}C$
Operating Junction Temperature	T_j	-55 to +150	$^{\circ}C$

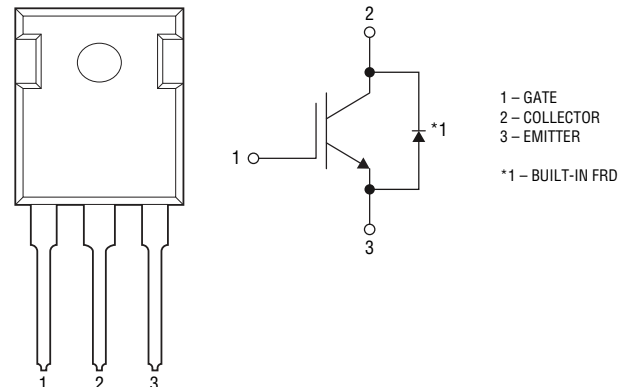
Thermal Resistance

Parameter	Symbol	Max	Unit
IGBT Thermal Resistance Junction - Case	$R_{th(j-c)}_{IGBT}$	0.54	$^{\circ}C/W$
Diode Thermal Resistance Junction - Case	$R_{th(j-c)}_{Diode}$	1.2	$^{\circ}C/W$

Typical Part Marking



Internal Circuit



*RoHS Directive 2015/863, Mar 31, 2015 and Annex.
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BIDW30N60T Insulated Gate Bipolar Transistor (IGBT)

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Static Electrical Characteristics ($T_C = 25\text{ }^\circ\text{C}$, Unless Otherwise Specified)

Parameter	Symbol	Conditions	Value			Unit
			Min.	Typ.	Max.	
Collector-Emitter Breakdown Voltage	BV_{CES}	$V_{GE} = 0\text{ V}, I_C = 250\text{ }\mu\text{A}$	600	—	—	V
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$V_{GE} = 15\text{ V}, I_C = 30\text{ A}$ $T_C = 25\text{ }^\circ\text{C}$	—	1.65	—	V
		$V_{GE} = 15\text{ V}, I_C = 30\text{ A}$ $T_C = 125\text{ }^\circ\text{C}$	—	1.9	—	
Diode Forward On-Voltage	V_F	$I_F = 30\text{ A}, T_C = 25\text{ }^\circ\text{C}$	—	1.8	—	V
		$I_F = 30\text{ A}, T_C = 125\text{ }^\circ\text{C}$	—	1.5	—	V
Gate Threshold Voltage	$V_{GE(th)}$	$V_{CE} = V_{GE}, I_C = 250\text{ }\mu\text{A}$	4.0	5.0	6.5	V
Collector Cut-off Current	I_{CES}	$V_{GE} = 0\text{ V}, V_{CE} = 600\text{ V}$	—	—	200	μA
Gate-Emitter Leakage Current	I_{GES}	$V_{CE} = 0\text{ V}, V_{GE} = \pm 20\text{ V}$	—	—	± 400	nA

Dynamic Electrical Characteristics ($T_C = 25\text{ }^\circ\text{C}$, Unless Otherwise Specified)

Parameter	Symbol	Conditions	Value			Unit
			Min.	Typ.	Max.	
Input Capacitance	C_{ies}	$V_{CE} = 30\text{ V}, V_{GE} = 0\text{ V},$ $f = 1\text{ MHz}$	—	1650	—	pF
Output Capacitance	C_{oes}		—	130	—	
Reverse Transfer Capacitance	C_{res}		—	35	—	
Total Gate Charge	Q_g	$V_{CE} = 400\text{ V}, V_{GE} = 15\text{ V}$ $I_C = 30.0\text{ A}$	—	76	—	nC
Gate-Emitter Charge	Q_{ge}		—	20	—	
Gate-Collector Charge	Q_{gc}		—	38	—	

IGBT Switching Characteristics (Inductive Load, $T_C = 25\text{ }^\circ\text{C}$, unless otherwise specified)

Parameter	Symbol	Conditions	Value			Unit
			Min.	Typ.	Max.	
Turn-on Delay Time	$t_{d(on)}$	$V_{CE} = 400\text{ V}, V_{GE} = 15\text{ V}$ $I_C = 30.0\text{ A}, R_G = 10\text{ }\Omega$	—	30	—	ns
Current Rise Time	t_r		—	105	—	ns
Turn-off Delay Time	$t_{d(off)}$		—	67	—	ns
Current Fall Time	t_f		—	100	—	ns
Turn-on Switching Energy	E_{on}		—	1.85	—	mJ
Turn-off Switching Energy	E_{off}		—	0.45	—	mJ
Total Switching Energy	E_{ts}		—	2.3	—	mJ

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BIDW30N60T Insulated Gate Bipolar Transistor (IGBT)

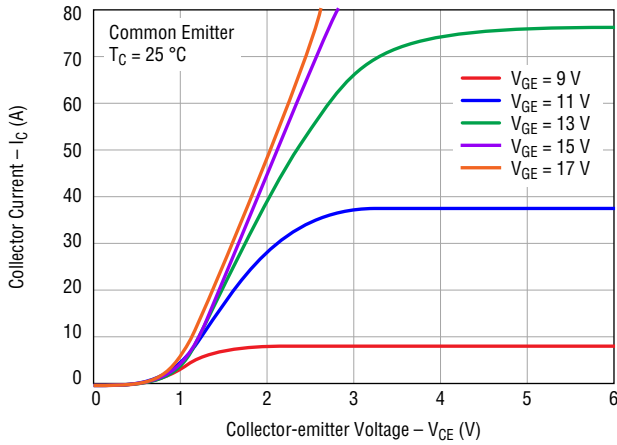


Diode Switching Characteristics ($T_C = 25\text{ }^\circ\text{C}$, unless otherwise specified)

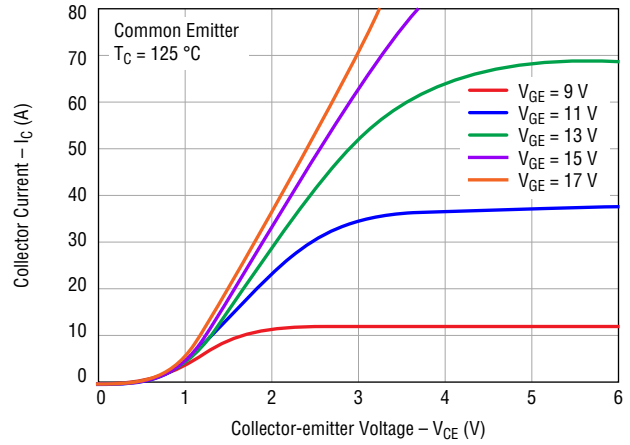
Parameter	Symbol	Conditions	Value			Unit
			Min.	Typ.	Max.	
Reverse Recovery Time	t_{rr}	$di_F/dt = 200\text{ A}/\mu\text{s}$ $I_F = 30.0\text{ A}$	—	40	—	ns
Reverse Recovery Charge	Q_{rr}		—	90	—	nC

Electrical Characteristic Performance

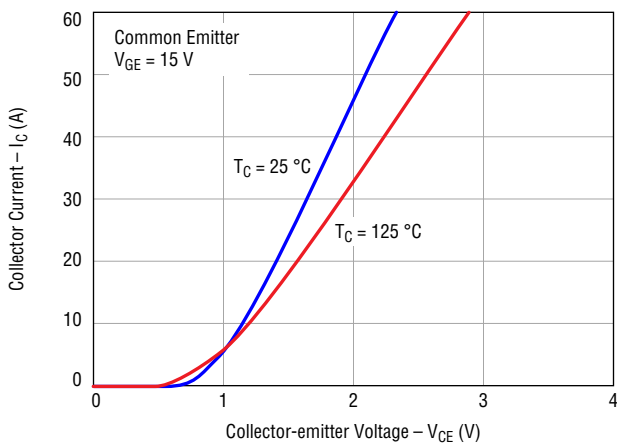
Typical Output Characteristics



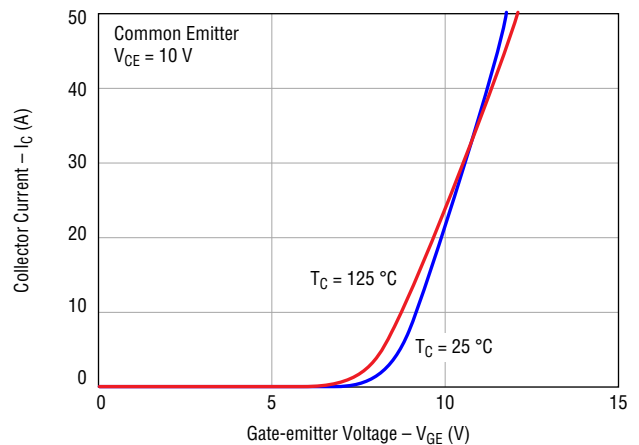
Typical Output Characteristics



Typical Saturation Voltage Characteristics



Typical Transfer Characteristics



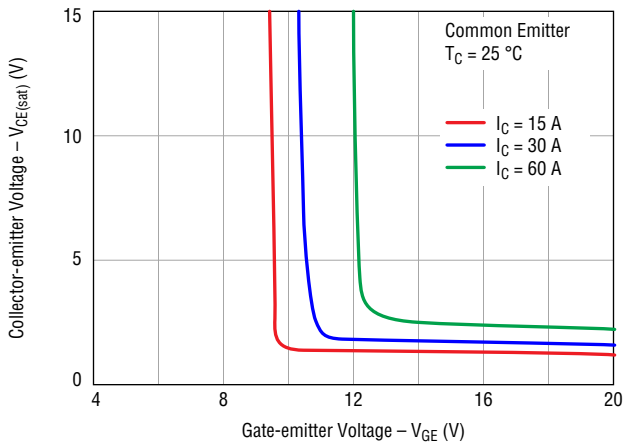
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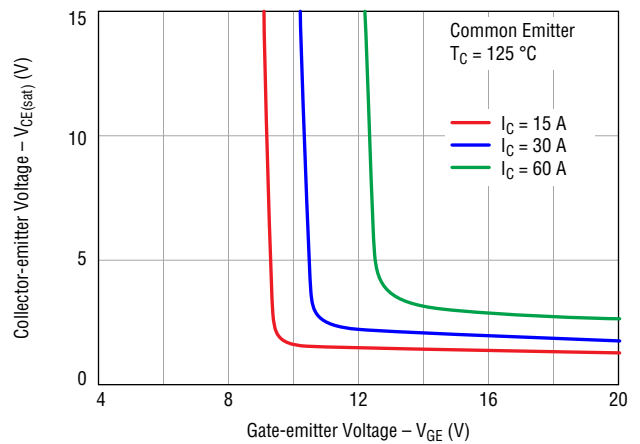
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Electrical Characteristic Performance (continued)

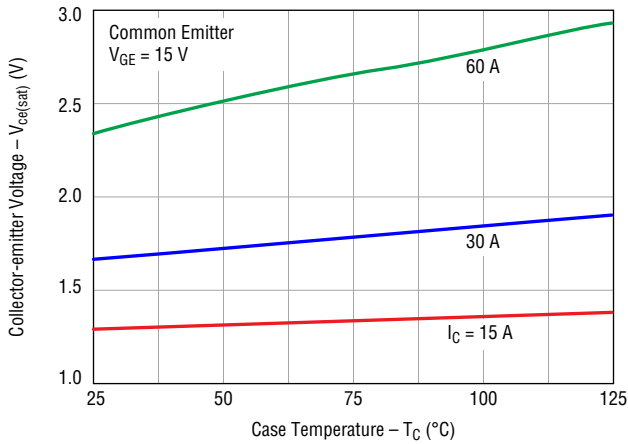
Typical $V_{CE(sat)}$ vs V_{GE} @ $T_C = 25^\circ\text{C}$



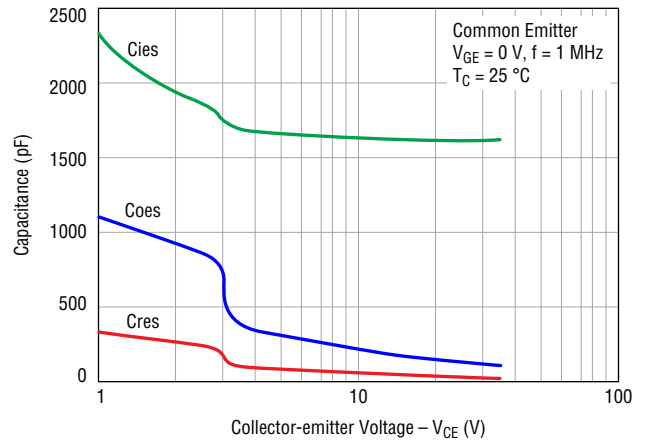
Typical $V_{CE(sat)}$ vs V_{GE} @ $T_C = 125^\circ\text{C}$



Typical $V_{CE(sat)}$ vs Case Temperature



Typical Capacitance Characteristics



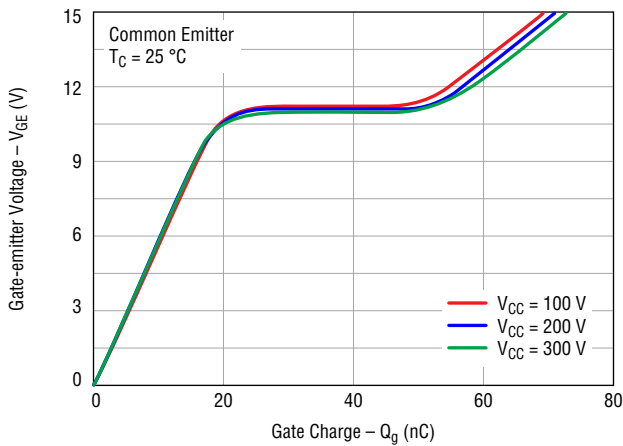
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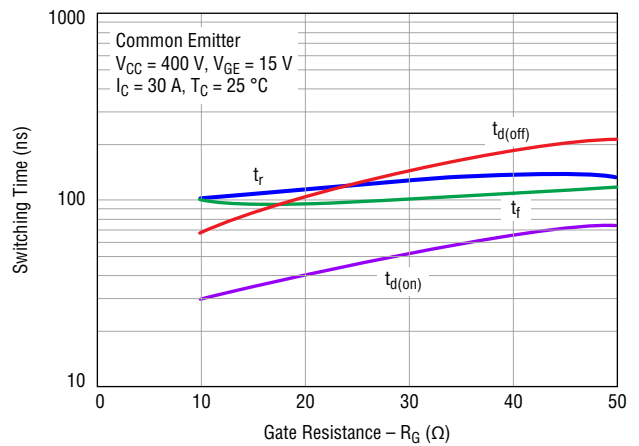
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Electrical Characteristic Performance (continued)

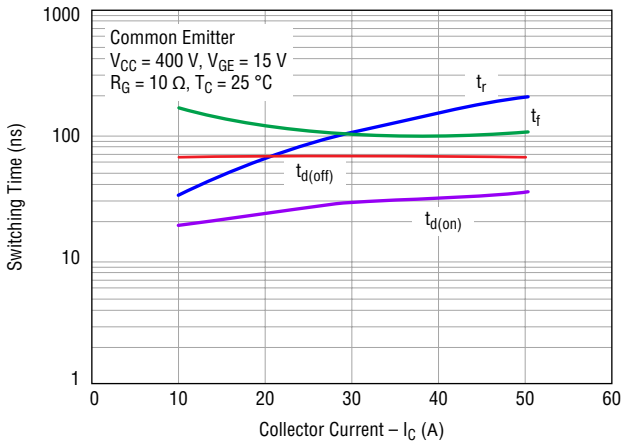
Typical Gate Charge Characteristics



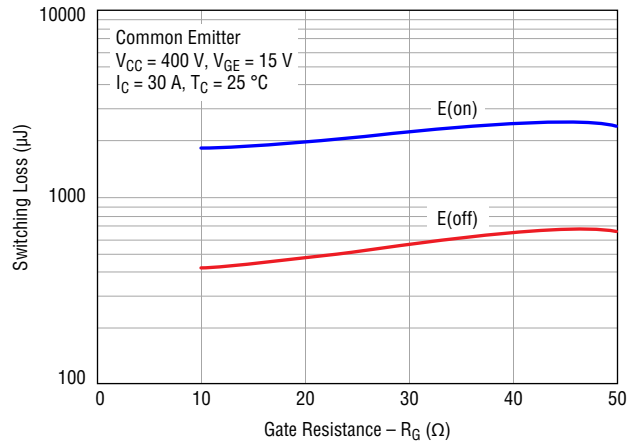
Typical Switching Time Characteristics vs R_G



Typical Switching Time Characteristics vs I_C



Typical Switching Loss vs R_G



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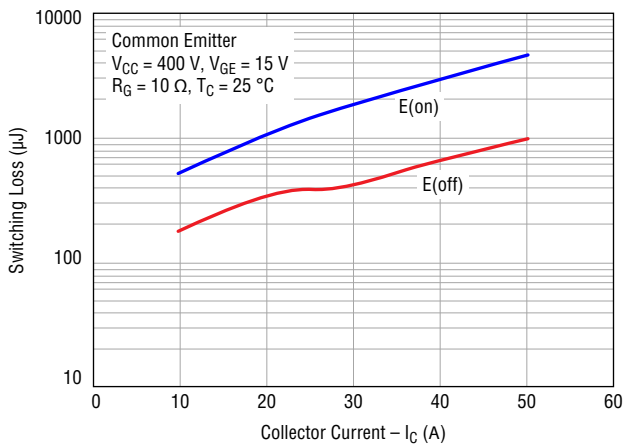
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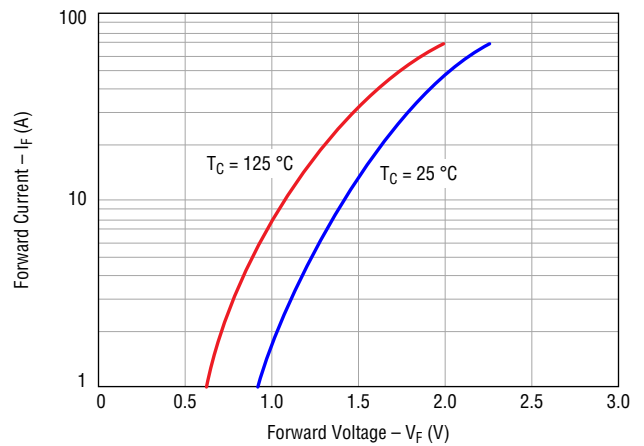
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Electrical Characteristic Performance (continued)

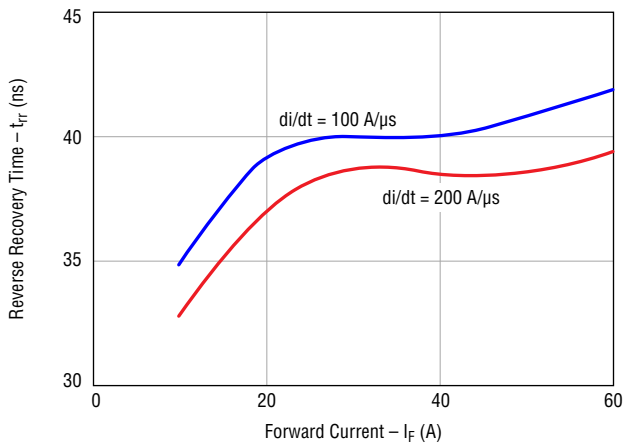
Typical Switching Loss Characteristics vs I_C



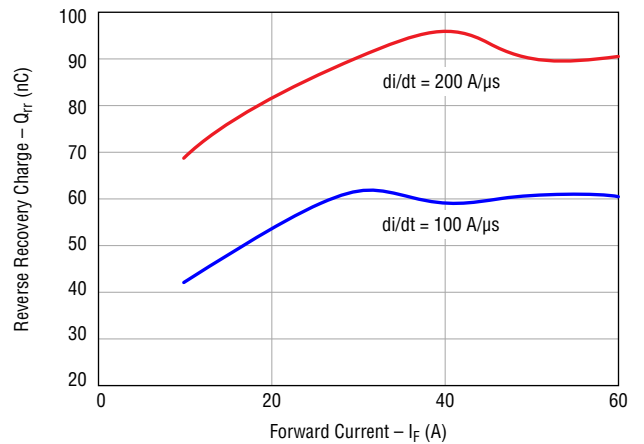
Typical Diode I_F vs V_F



Typical Reverse Recovery Time vs I_F



Typical Reverse Recovery Charge vs I_F



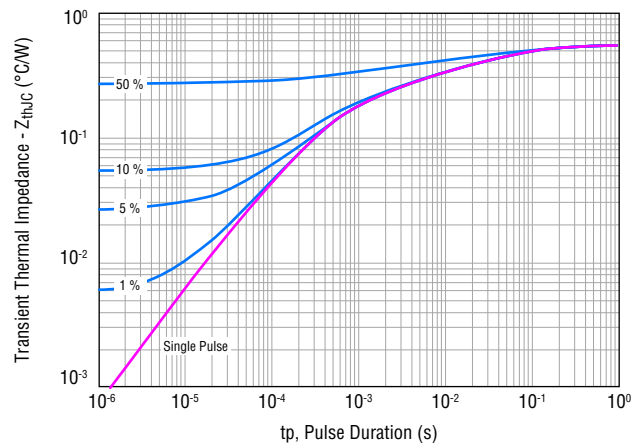
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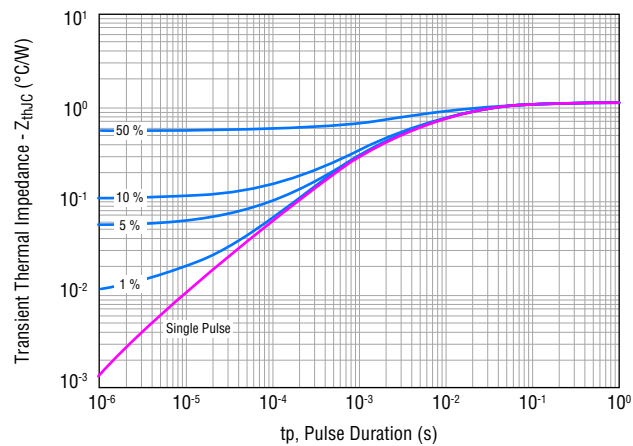
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Electrical Characteristic Performance (continued)

IGBT Transient Thermal Impedance vs $t_{p(ON)}$ Duration ($D=t_p/T$)



Diode Transient Thermal Impedance vs $t_{p(ON)}$ Duration ($D=t_p/T$)



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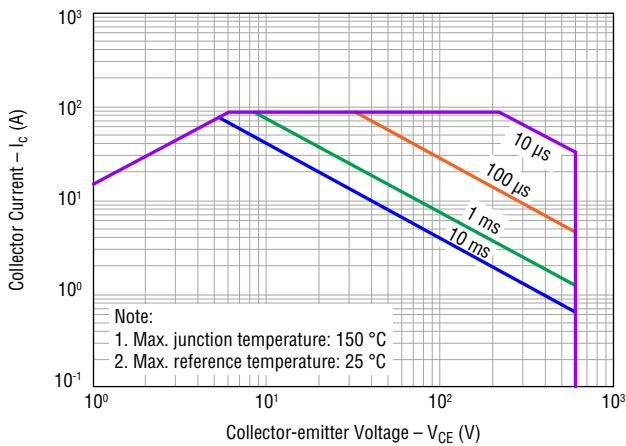
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BIDW30N60T Insulated Gate Bipolar Transistor (IGBT)



Electrical Characteristic Performance (continued)

Forward Bias Safe Operating Area

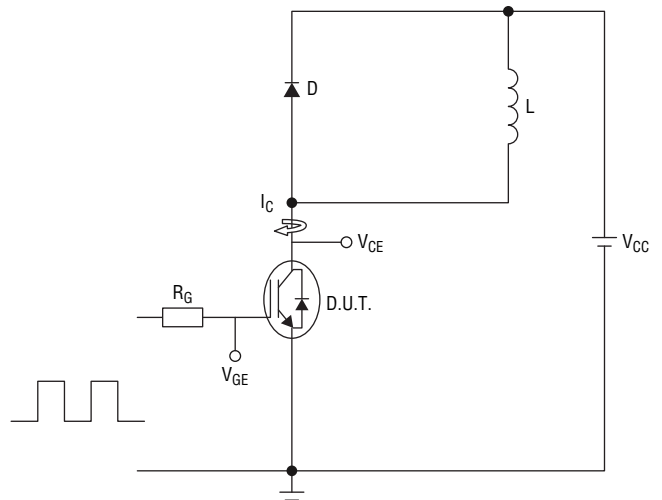


How to Order

B I D W 30 N 60 T

- B = Bourns®
- I = IGBT
- Type
D = Discrete
- Package Code
W = TO-247
- Current Rating
30 = 30 A
- Device Type
N = N-channel
- Nominal Voltage (divided by 10)
60 = 600 V
- Optimization
T = Medium Speed

Inductive Load Test Circuit



$L = 1.87 \text{ mH}$, $V_{CE} = 400 \text{ V}$, $V_{GE} = 15 \text{ V}$, $I_C = 30 \text{ A}$, $R_G = 10 \Omega$

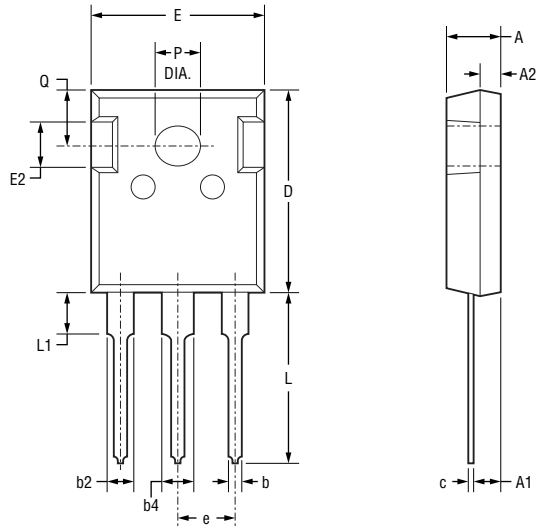
Environmental Characteristics

ESD Class (HBM) 2

BIDW30N60T Insulated Gate Bipolar Transistor (IGBT)

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Product Dimensions



DIMENSIONS: $\frac{\text{MM}}{\text{(INCHES)}}$

Symbol	Min.	Nom.	Max.
A	$\frac{4.80}{(.189)}$	$\frac{5.00}{(.197)}$	$\frac{5.20}{(.205)}$
A1	$\frac{2.21}{(.087)}$	$\frac{2.41}{(.095)}$	$\frac{2.59}{(.102)}$
A2	$\frac{1.85}{(.073)}$	$\frac{2.00}{(.079)}$	$\frac{2.15}{(.085)}$
b	$\frac{1.11}{(.044)}$	—	$\frac{1.36}{(.054)}$
b2	$\frac{1.91}{(.075)}$	—	$\frac{2.25}{(.089)}$
b4	$\frac{2.91}{(.115)}$	—	$\frac{3.25}{(.128)}$
c	$\frac{0.51}{(.020)}$	—	$\frac{0.75}{(.030)}$
D	$\frac{20.80}{(.819)}$	$\frac{21.00}{(.827)}$	$\frac{21.30}{(.839)}$
E	$\frac{15.50}{(.610)}$	$\frac{15.80}{(.622)}$	$\frac{16.10}{(.634)}$
E2	$\frac{4.40}{(.173)}$	$\frac{5.00}{(.197)}$	$\frac{5.20}{(.205)}$
e	$\frac{5.44}{(.214)} \text{ BSC}$		
L	$\frac{19.72}{(.776)}$	$\frac{19.92}{(.784)}$	$\frac{20.22}{(.796)}$
L1	—	—	$\frac{4.30}{(.169)}$
P	$\frac{3.40}{(.134)}$	—	$\frac{3.80}{(.150)}$
Q	$\frac{5.60}{(.220)}$	$\frac{5.80}{(.228)}$	$\frac{6.00}{(.236)}$

Packaging Specifications

BIDW30N60T 30 pieces per tube

BOURNS®

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